

BAT85/86(For Glass Seal)

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Chip Information

Chip Size	0.39 x 0.39mm
Pad Size	0.30 x 0.30mm
Chip Quantity	72690 pcs/wafer
Scribe Line Width	50um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Ag Bump 30um(For Glass Seal)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	50	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	50	V	
Average Forward Rectified Current	IF(AV)	200	mA	
Peak Forward Surge Current	IFSM	5	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Test Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.800	0.790	0.600	V	IF=100mA Ta=25degC
	VF2	0.500	0.490	0.415	V	IF=30mA Ta=25degC
	VF3	0.400	0.390	0.340	V	IF=10mA Ta=25degC
	VF4	0.320	0.315	0.260	V	IF=1mA Ta=25degC
	VF5	0.240	0.235	0.200	V	IF=100uA Ta=25degC
Maximum DC Reverse Current	IR1	2	1	0.3	uA	VR=25V Ta=25degC
	IR2	5	3	0.4	uA	VR=40V Ta=25degC
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV1	50	55	70	V	IR=100uA
	BV2	50	55	70	V	IR=500uA
	deltaBV	2.5	2		V	BV2-BV1
Junction Capacitance	Cj			7	pF	V=1V,f=1MHz
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
YFS17A	200 +/- 20um	Ti-Ni-Ag(For Glass Seal)

Note:
Designed For BAT85/86